

# 100nm depth oxide HM (C60P120) Via navigation & results

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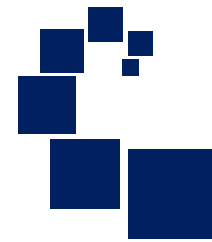
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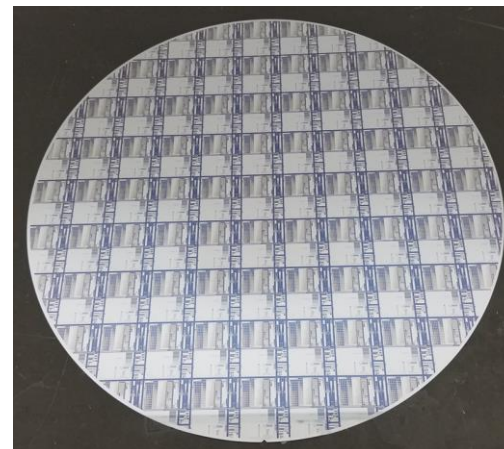


# AMAG7A pane is pattern on HARhole wafers



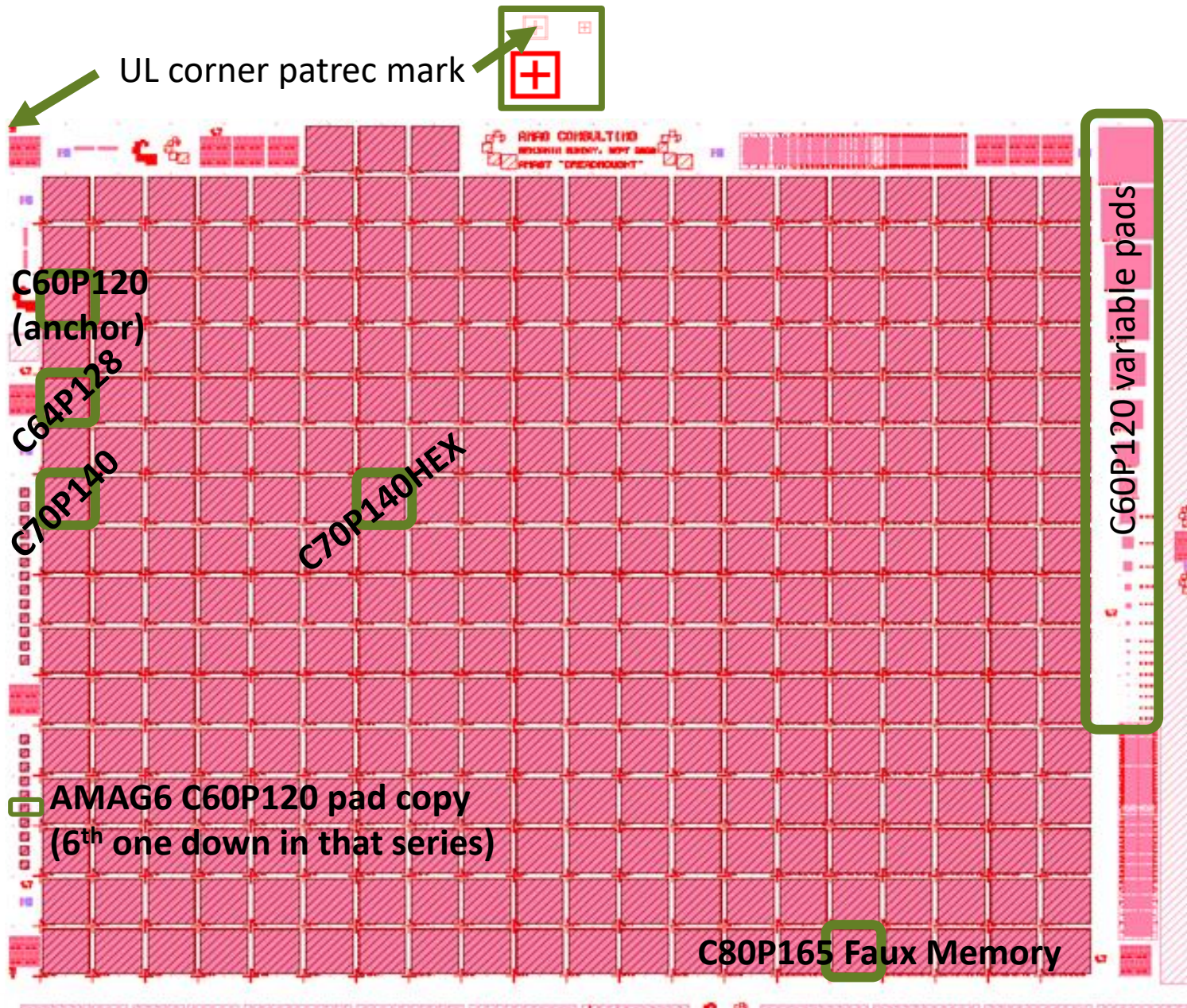
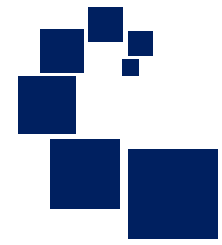
Pane  
AMAG7A:  
Darkfield  
content  
(hole,  
trench,  
variations)

- Full die repeat size is 26.000mm x 33.000mm (exactly).
- Pane A as shown is bladed to print the pattern leaving much empty space filling in ~60% area of die, important for etch loading control to achieve the etch.
- Only the pattern circled in orange to left is present, as that is the content with holes and trenches; the rest is for line/space which does not pattern at same conditions so is omitted for etch loading and defectivity reasons.

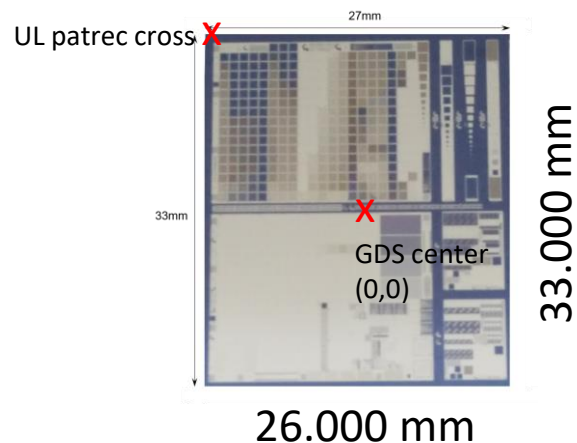
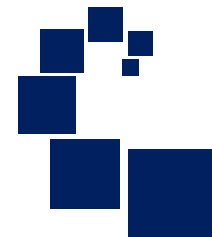




# AMAG7A pane is main pattern on HM100 Via wafers



# AMAG7A pane is main pattern on HARhole wafers



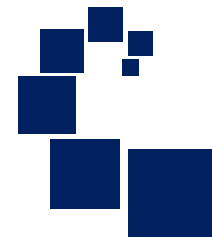
Photograph of Via pattern

(rough pattern between die is just reflection off ceiling)

Pattern	Wafer Type	x [um]	y [um]	Tile coordinates (each tile has location in GDS)
UL pattern rec cross--top left corner of die	100Hm Via	-12920.5	15930.7	left of A-00
AMAG7 C60P120 grating (anchor target, 800um pad)	100Hm Via	-12040	12650	A-03
C70P140 grating (800um pad)	100Hm Via	-12040	9150	A-07
C70P140HEX grating (800um pad)	100Hm Via	-6600	9150	G-07
C80P165 Faux Memory grating (800um pad)	100Hm Via	1473	1067	P-16
AMAG6 C60P120 grating (150um pad)	100Hm Via	-12720	3633	left of A-13
GDS center (cartesian coordinates)	no feature	0	0	~center of bottom of patterned area

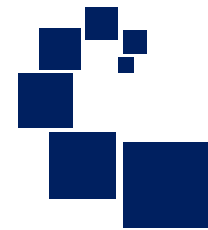


# Via HM100 wafer-level CD results



- This report shows the wafer-level averages and variation for each wafer of the first lot of the Via product.
- Specific maps for each wafer including the average & 1sigma and SEM images of all-die of C60P120 and few sites of each of the secondary targets.
- CD values convey top CD of the holes.
  - For C80P165 Faux Memory, two values represent the holes nearest trench and holes further from trench.

<b>Lot ID:</b> 2240EMEM001.000								
<b>Purpose:</b> AMAG7, Full Reticle, Via etched in 100nm Oxide. Anchor feature = C60 P120								
		Final CDSEM measurements (nm)						
		recipe = DNVA1FAMAG7XCDU1			recipe = DNVA1FAMAG7XCDU2			
Slot	Wfr ID	C60 P120 (XCH) All Die CD	C60 P120 (1-sigma)	C70 P140 HEX (NCH) 11 die	C64 P128 (ACH) 11 die	C70 P140 (BCH) 11 die	C80 P165 MEM (ECH) CD1, 11 die	C80 P165 MEM (ECH2) CD2, 11 die
1	46JVS155SJD1	82.00	1.83	66.5	72.9	86.6	97.8	95.7
2	46JVS156SJA0	53.44	1.73	67.3	72.7	86.1	96.6	94.9
3	46JVG041SJA1	53.33	1.77	67.4	72.6	86.3	96.3	94.6
4	46ZS107SJG5	58.66	1.77	73.3	76.7	89.5	81.1	97.3
5	46ZS106SJC3	54.33	1.73	68.6	72.7	85.7	81.7	92.8
Lot	Averages	60.35	1.77	68.6	73.5	86.8	90.7	95.1



# 46JVS155SJD1(2240EMEM001 slot 1) Reference Data

## C60P120 Anchor Target

Oct 2022

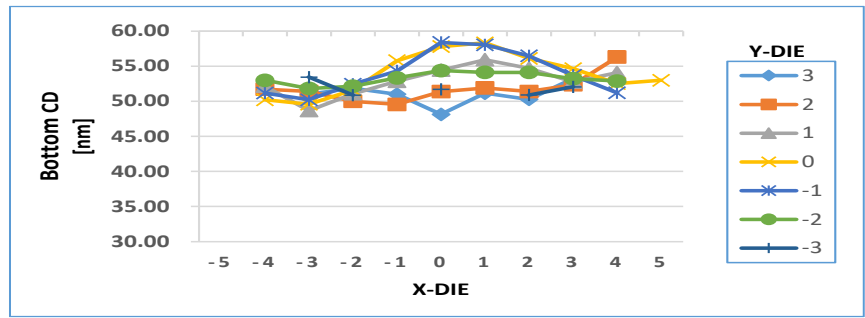
- All measurements in nm.
- Avg CD and 1sigma line-to-line variation for C60P120 anchor target for each die, reported for each die in wafer map format, and plotted to right.
- Average and 1sigma values are of 8 lines sampled at each site, from images on next page.
- CD values convey top CD of the holes.

Full Wafer Avg CD:	52.82	nm
Full wafer 1sigma CD:	2.36	nm
Die-to-Die 1sigma		
Avg:	1.83	nm
RMS:	1.86	nm
Ellipticity Avg:	1.06	
FOV:	800	nm

Average of all individual die CD averages (25 targets/die).  
 Stdev of all die CD average of (25 targets/die), represents across wafer variation.  
 Feature-to-feature variation within grating.  
 Arithmetic average value of feature-to-feature variation.  
 RMS average value of feature-to-feature variation.  
 Average of ratio of major axis to minor axis.  
 Size of image (field-of-view).

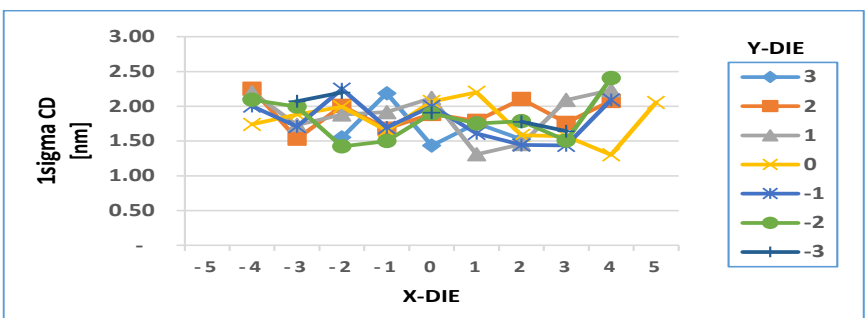
### C60P120 Anchor Target Avg CD (line)

	-5	-4	-3	-2	-1	0	1	2	3	4	5
3			51.02	51.86	51.01	48.15	51.16	50.28	53.24		
2		51.73	51.41	50.01	49.57	51.39	51.92	51.40	52.36	56.32	
1		52.16	48.68	51.07	52.87	54.44	55.93	54.71	52.76	54.09	
0		50.23	49.59	51.62	55.80	57.81	58.35	56.13	54.66	52.53	53.01
-1		51.19	50.23	52.44	54.33	58.39	58.07	56.49	53.72	51.22	
-2		53.00	51.85	52.16	53.34	54.39	54.13	54.13	53.22	52.89	
-3			53.44	50.89		51.70		50.90	52.07		



### C60P120 Anchor Target 1sigma CD

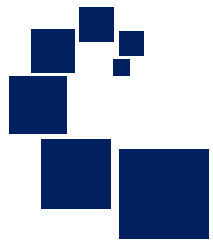
	-5	-4	-3	-2	-1	0	1	2	3	4	5
3				1.55	2.19	1.43	1.76	1.53			
2		2.25	1.53	2.01	1.68	1.89	1.79	2.10	1.76	2.08	
1		2.20	1.73	1.88	1.92	2.12	1.31	1.46	2.09	2.23	
0		1.74	1.88	1.99	1.65	2.07	2.20	1.58	1.57	1.30	2.06
-1		2.00	1.71	2.25	1.69	2.00	1.61	1.44	1.44	2.09	
-2		2.10	1.99	1.42	1.50	1.90	1.75	1.79	1.51	2.41	
-3			2.07	2.20		1.91		1.78	1.64		



# 46JVS155SJD1(2240EMEM001 slot 1) Reference Data

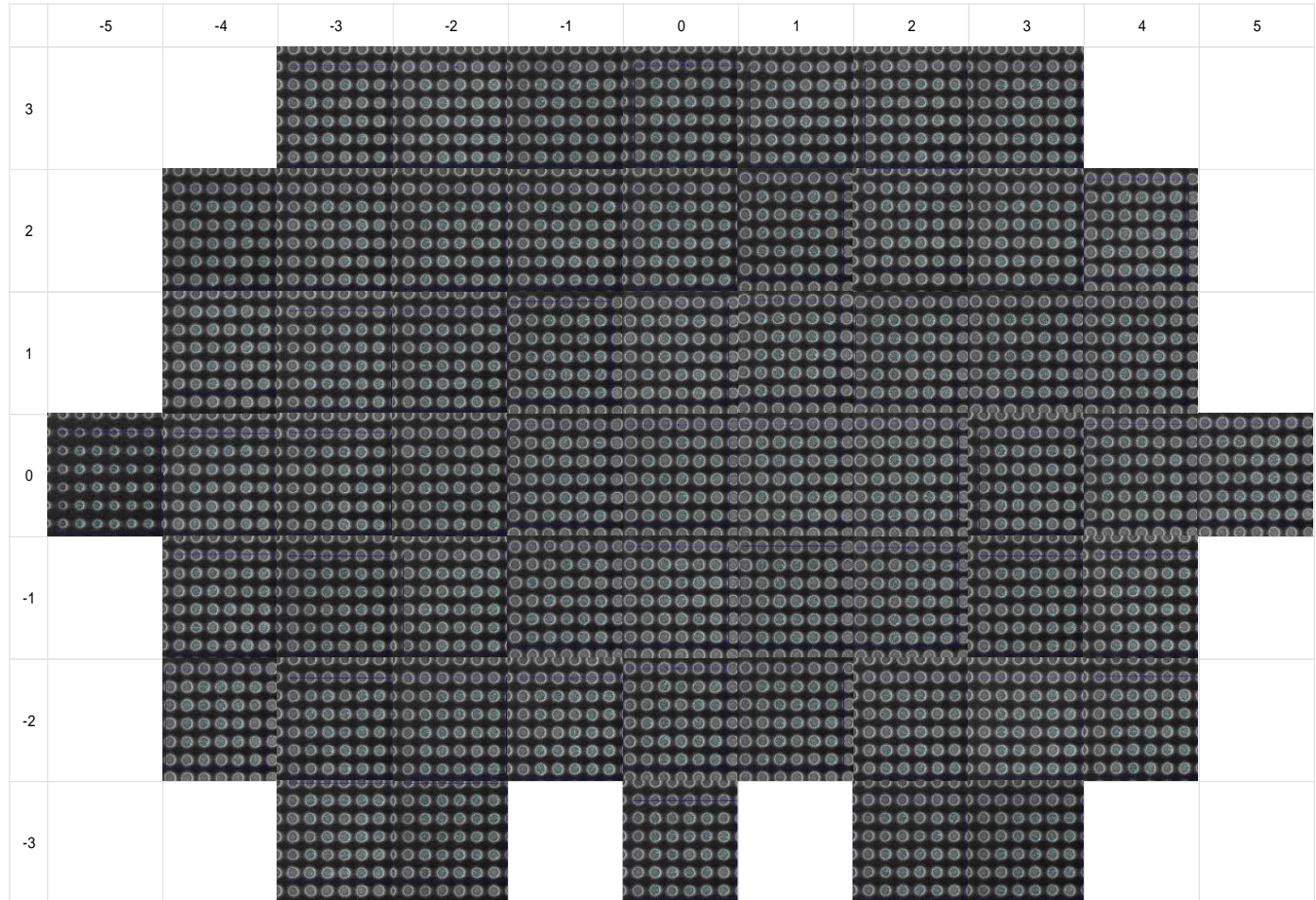
C60P120 Anchor Target

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## C60P120 Anchor Target CD-SEM image wafer map

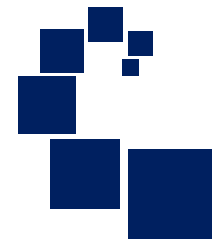
Full Wafer Avg CD:	52.82	nm
Full wafer 1sigma CD:	2.36	nm
Die-to-Die 1sigma		
Avg:	1.83	nm
RMS:	1.86	nm
Ellipticity Avg:	1.06	
FOV:	800	nm



# 46JVS155SJD1(2240EMEM001 slot 1) Reference Data

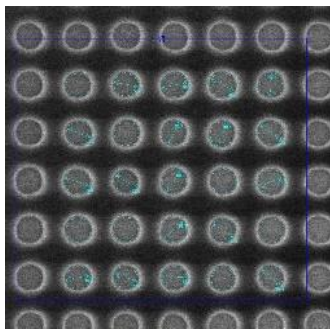
C60P120 Anchor Target

Oct 2022



## Anchor Target

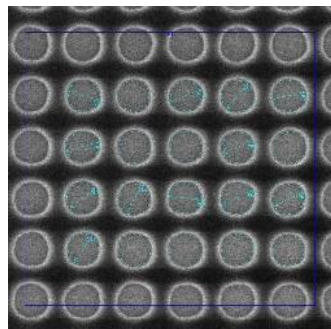
C60P120 (XCH\*)



Full Wafer Avg CD:	52.82	nm
Full wafer 1sigma CD:	2.36	nm
Die-to-Die 1sigma		
Avg:	1.83	nm
RMS:	1.86	nm
Ellipticity Avg:	1.06	
FOV:	800	nm

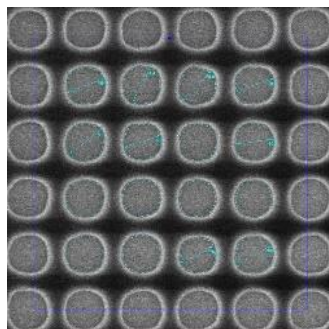
## Secondary Targets

C64P128 (ACH\*)



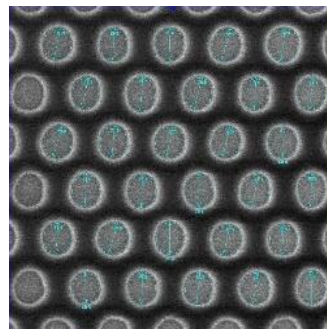
Full Wafer Avg CD:	72.9	nm
Full wafer 1sigma CD:	1.91	nm
Die-to-Die 1 sigma:		
Avg:	1.42	nm
RMS:	1.45	nm
Ellipticity Avg:	1.05	
FOV:	800	nm

C70P140 (BCH\*)



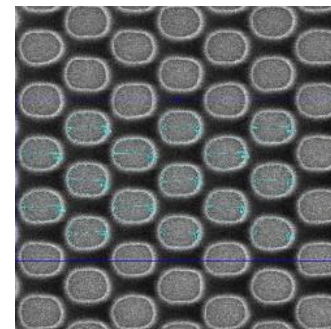
Full Wafer Avg CD:	86.6	nm
Full wafer 1sigma CD:	1.70	nm
Die-to-Die 1 sigma:		
Avg:	1.27	nm
RMS:	1.28	nm
Ellipticity Avg:	1.04	
FOV:	800	nm

C70P140HEX (NCH\*)



Full Wafer Avg CD:	66.50	nm
Full wafer 1sigma CD:	2.23	nm
Die-to-Die 1 sigma		
Avg:	1.73	nm
RMS:	1.75	nm
Ellipticity Avg:	1.21	
FOV:	800	nm

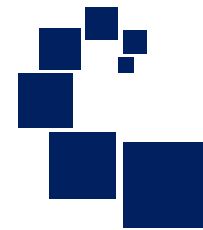
C80P165MEM (ECH2\*)



Full Wafer Avg CD:	95.7	nm
Full wafer 1sigma CD:	1.96	nm
Die-to-Die 1 sigma		
Avg:	3.01	nm
RMS:	3.21	nm
Ellipticity Avg:	5.12	
FOV:	1000	nm

\* Coding labels for CD data results files





# 46JVS156SJA0(2240EMEM001 slot 2) Reference Data

## C60P120 Anchor Target

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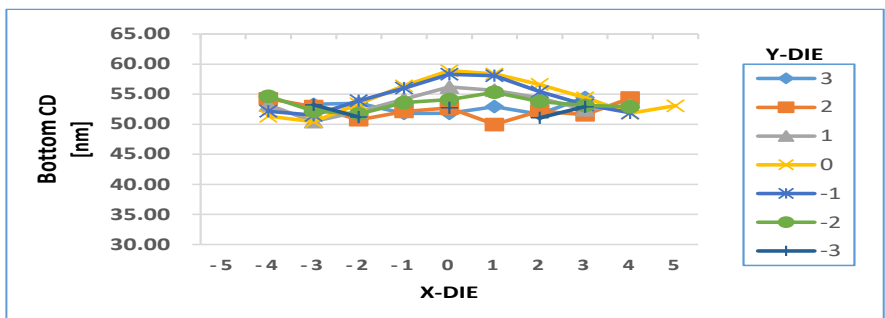
- All measurements in nm.
- Avg CD and 1sigma line-to-line variation for C60P120 anchor target for each die, reported for each die in wafer map format, and plotted to right.
- Average and 1sigma values are of 8 lines sampled at each site, from images on next page.
- CD values convey top CD of the holes.

Full Wafer Avg CD:	53.44	nm
Full wafer 1sigma CD:	2.05	nm
Die-to-Die 1sigma		
Avg:	1.73	nm
RMS:	1.74	nm
Ellipticity Avg:	1.05	
FOV:	800	nm

Average of all individual die CD averages (25 targets/die).  
 Stdev of all die CD average of (25 targets/die), represents across wafer variation.  
 Feature-to-feature variation within grating.  
 Arithmetic average value of feature-to-feature variation.  
 RMS average value of feature-to-feature variation.  
 Average of ratio of major axis to minor axis.  
 Size of image (field-of-view).

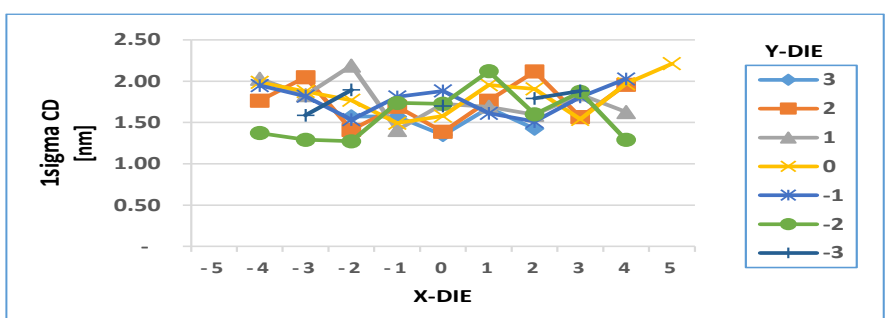
### C60P120 Anchor Target Avg CD (line)

	-5	-4	-3	-2	-1	0	1	2	3	4	5
3			53.32	53.50	51.79	51.81	52.92	51.68	54.44		
2		54.24	52.94	50.74	52.12	52.70	49.96	52.18	51.57	54.34	
1		53.18	50.43	52.10	54.19	56.19	55.64	54.36	52.42	53.08	
0		51.32	50.41	53.39	56.40	58.90	58.38	56.61	54.40	51.82	53.08
-1		52.15	51.49	53.89	56.00	58.32	58.07	55.41	53.23	51.89	
-2		54.65	52.18	51.72	53.59	54.09	55.33	53.78	53.10	52.91	
-3			53.23	51.19		52.73		51.06	52.91		



### C60P120 Anchor Target 1sigma CD

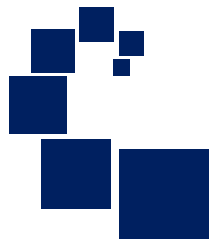
	-5	-4	-3	-2	-1	0	1	2	3	4	5
3				1.57	1.57	1.35	1.68	1.42			
2		1.76	2.05	1.41	1.69	1.39	1.76	2.12	1.56	1.96	
1		2.03	1.83	2.19	1.41	1.73	1.69	1.59	1.84	1.63	
0		1.99	1.88	1.77	1.49	1.58	1.96	1.91	1.54	1.97	2.21
-1		1.95	1.82	1.53	1.81	1.88	1.61	1.51	1.81	2.03	
-2		1.37	1.29	1.27	1.74	1.73	2.12	1.60	1.87	1.29	
-3			1.59	1.90		1.70		1.79	1.88		



# 46JVS156SJA0(2240EMEM001 slot 2) Reference Data

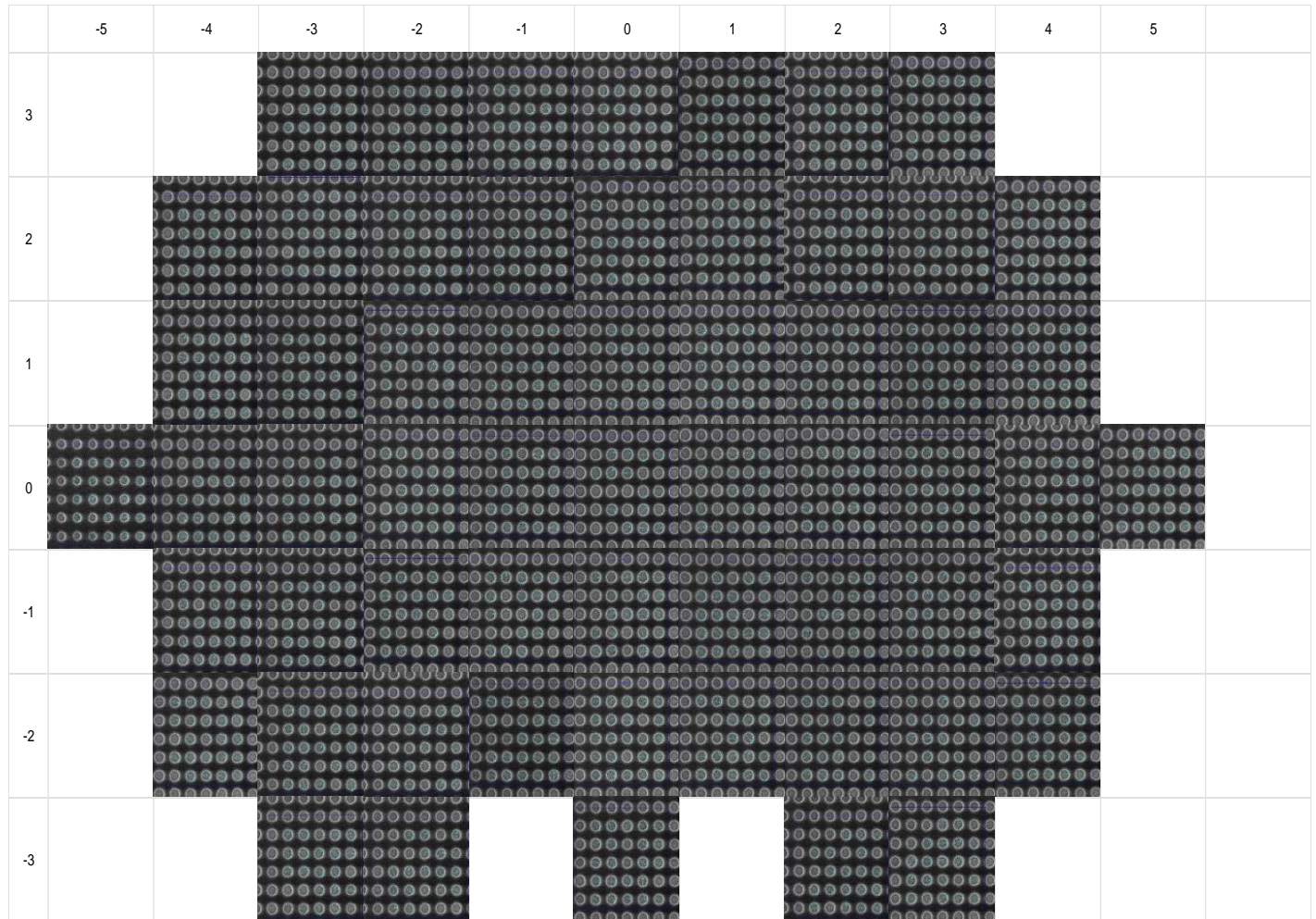
C60P120Anchor Target

Oct 2022



## C60P120 Anchor Target CD-SEM image wafer map

Full Wafer Avg CD:	53.44	nm
Full wafer 1sigma CD:	2.05	nm
Die-to-Die 1sigma	Avg:	1.73 nm
	RMS:	1.74 nm
Ellipticity Avg:	1.05	
FOV:	800	nm

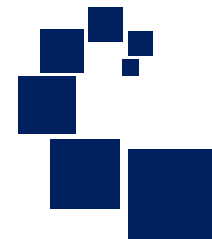




# 46JVS156SJA0(2240EMEM001 slot 2) Reference Data

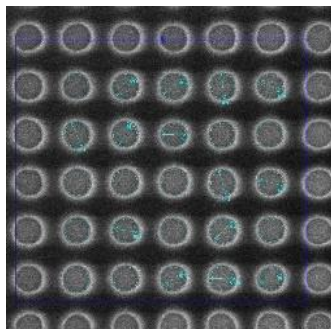
C60P120 Anchor Target

Oct 2022



## Anchor Target

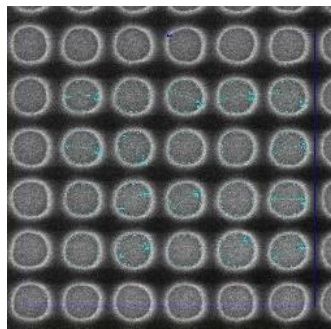
C60P120 (XCH\*)



Full Wafer Avg CD:	53.44	nm
Full wafer 1sigma CD:	2.05	nm
Die-to-Die 1 sigma		
Avg:	1.73	nm
RMS:	1.74	nm
Ellipticity Avg:	1.05	
FOV:	800	nm

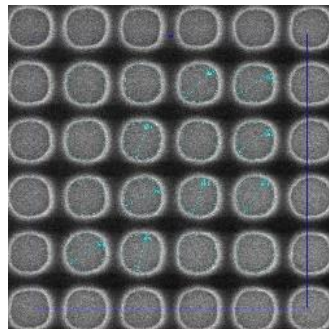
## Secondary Targets

C64P128 (ACH\*)



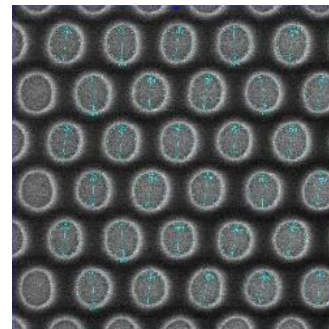
Full Wafer Avg CD:	72.7	nm
Full wafer 1sigma CD:	1.83	nm
Die-to-Die 1 sigma		
Avg:	1.44	nm
RMS:	1.46	nm
Ellipticity Avg:	1.04	
FOV:	800	nm

C70P140 (BCH\*)



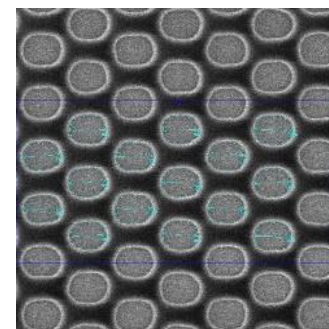
Full Wafer Avg CD:	86.1	nm
Full wafer 1sigma CD:	1.64	nm
Die-to-Die 1 sigma		
Avg:	1.21	nm
RMS:	1.22	nm
Ellipticity Avg:	1.04	
FOV:	800	nm

C70P140HEX (NCH\*)



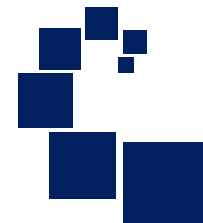
Full Wafer Avg CD:	67.28	nm
Full wafer 1sigma CD:	2.31	nm
Die-to-Die 1 sigma		
Avg:	1.67	nm
RMS:	1.68	nm
Ellipticity Avg:	1.21	
FOV:	800	nm

C80P165MEM (ECH2\*)



Full Wafer Avg CD:	94.9	nm
Full wafer 1sigma CD:	1.41	nm
Die-to-Die 1 sigma		
Avg:	1.43	nm
RMS:	1.54	nm
Ellipticity Avg:	1.25	
FOV:	1000	nm

\* Coding labels for CD data results files



# 46JVG041SJA1(2240EMEM001 slot 3) Reference Data

## C60P120 Anchor Target

Oct 2022

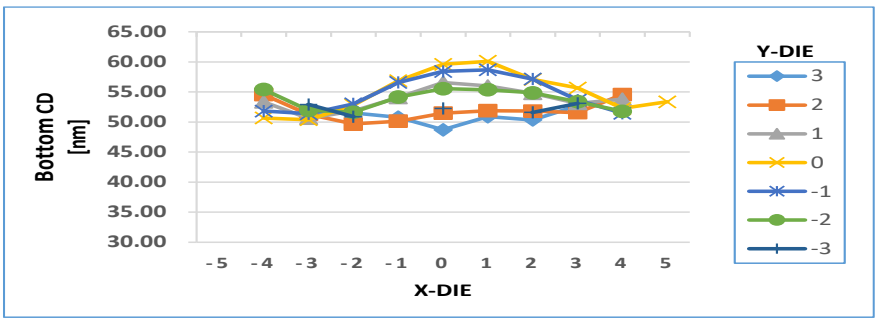
- All measurements in nm.
- Avg CD and 1sigma line-to-line variation for C60P120 anchor target for each die, reported for each die in wafer map format, and plotted to right.
- Average and 1sigma values are of 8 lines sampled at each site, from images on next page.
- CD values convey top CD of the holes.

Full Wafer Avg CD:	53.33	nm
Full wafer 1sigma CD:	2.58	nm
Die-to-Die 1sigma		
Avg:	1.75	nm
RMS:	1.77	nm
Ellipticity Avg:	1.05	
FOV:	800	nm

Average of all individual die CD averages (25 targets/die).  
 Stdev of all die CD average of (25 targets/die), represents across wafer variation.  
 Feature-to-feature variation within grating.  
 Arithmetic average value of feature-to-feature variation.  
 RMS average value of feature-to-feature variation.  
 Average of ratio of major axis to minor axis.  
 Size of image (field-of-view).

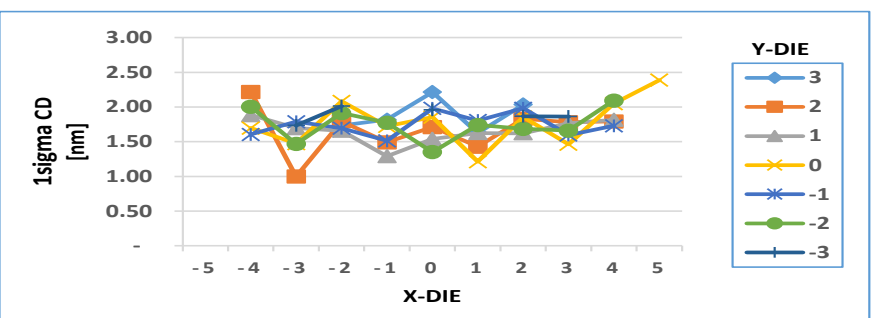
### C60P120 Anchor Target Avg CD (line)

	-5	-4	-3	-2	-1	0	1	2	3	4	5
3			51.48	51.51	50.78	48.69	50.89	50.33	52.73		
2		54.54	51.27	49.67	50.14	51.47	51.88	51.82	51.55	54.58	
1		53.33	50.62	51.84	54.09	56.57	55.98	54.77	53.08	53.79	
0		50.65	50.39	52.82	56.85	59.58	60.08	57.08	55.66	52.26	53.36
-1		51.82	51.38	53.02	56.56	58.42	58.68	57.13	53.63	51.46	
-2		55.40	51.94	51.60	54.14	55.54	55.35	54.84	53.38	51.77	
-3			52.90	50.89		52.26		51.59	53.08		



### C60P120 Anchor Target 1sigma CD

	-5	-4	-3	-2	-1	0	1	2	3	4	5
3				1.73	1.82	2.22	1.62	2.04			
2		2.22	1.00	1.79	1.49	1.71	1.43	1.83	1.78	1.79	
1		1.88	1.70	1.66	1.29	1.54	1.63	1.62	1.77	1.81	
0		1.70	1.47	2.08	1.72	1.85	1.21	1.86	1.46	2.05	2.39
-1		1.61	1.79	1.69	1.51	1.98	1.81	1.98	1.60	1.73	
-2		2.00	1.47	1.91	1.77	1.35	1.74	1.69	1.66	2.09	
-3			1.73	2.01		1.96		1.87	1.86		

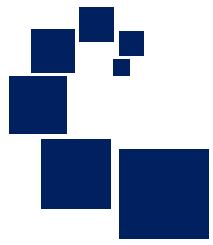




# 46JVG041SJA1(2240EMEM001 slot 3) Reference Data

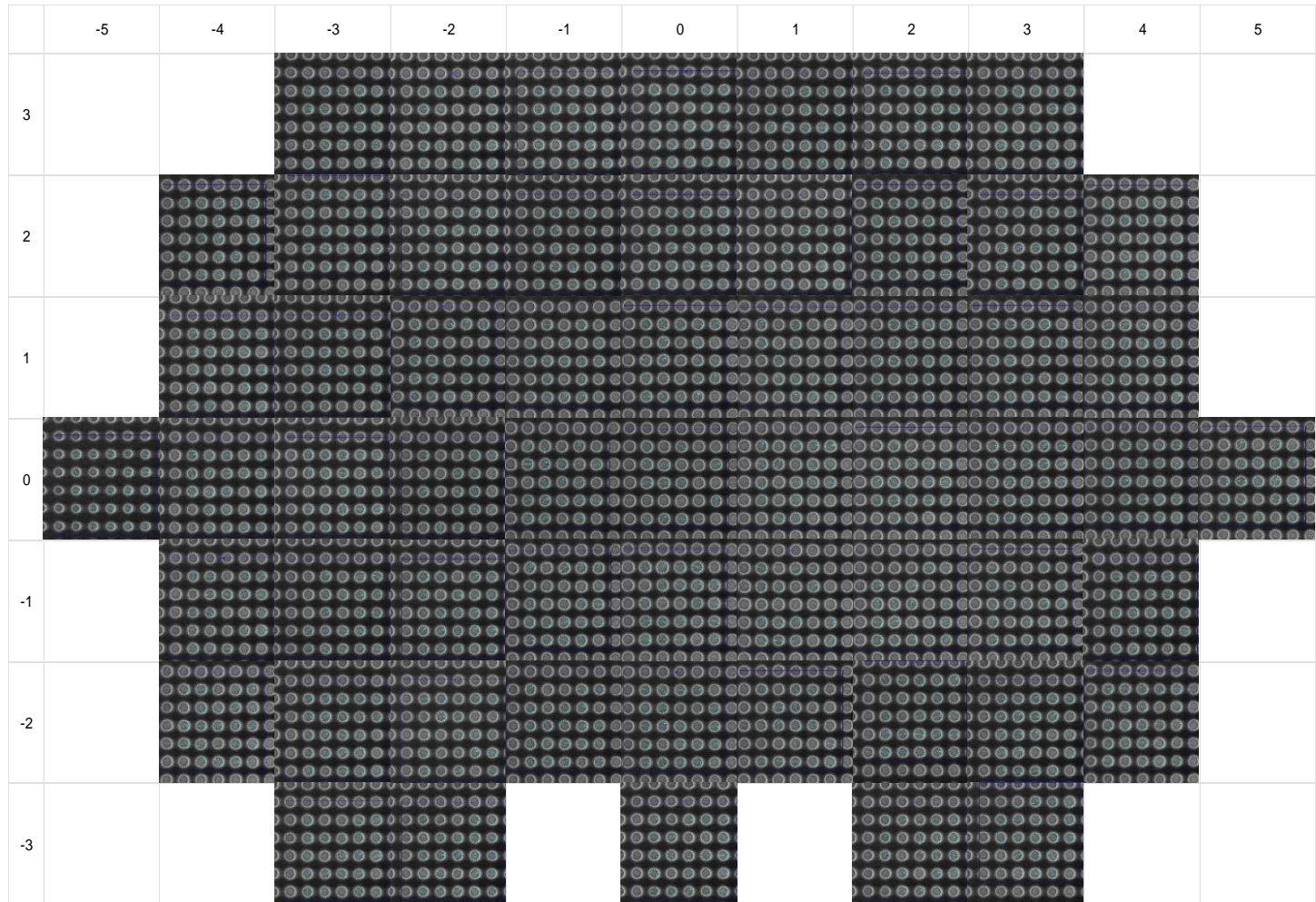
C60P120 Anchor Target

Oct 2022



C60P120 Anchor Target  
CD-SEM image wafer map

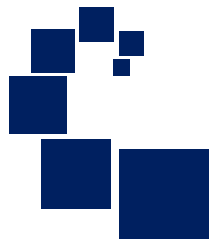
Full Wafer Avg CD:	53.33	nm
Full wafer 1sigma CD:	2.58	nm
Die-to-Die 1sigma		
Avg:	1.75	nm
RMS:	1.77	nm
Ellipticity Avg:	1.05	
FOV:	800	nm



# 46JVG041SJA1(2240EMEM001 slot 3) Reference Data

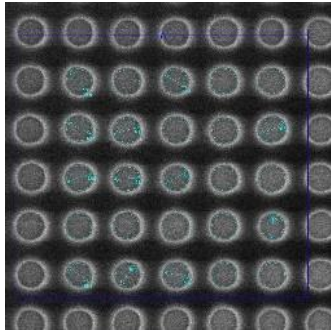
C60P120 Anchor Target

Oct 2022



## Anchor Target

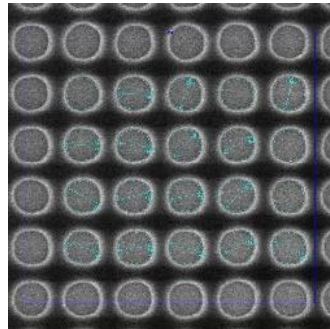
C60P120 (XCH\*)



Full Wafer Avg CD:	53.33	nm
Full wafer 1sigma CD:	2.58	nm
Die-to-Die 1sigma		
Avg:	1.75	nm
RMS:	1.77	nm
Ellipticity Avg:	1.05	
FOV:	800	nm

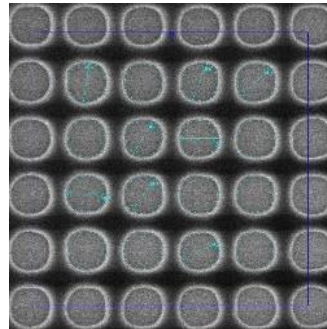
## Secondary Targets

C64P128 (ACH\*)



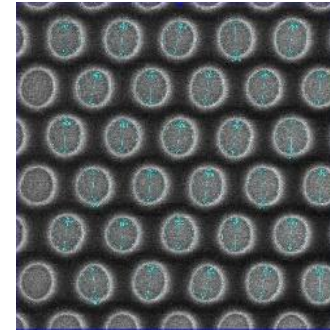
Full Wafer Avg CD:	72.6	nm
Full wafer 1sigma CD:	2.12	nm
Die-to-Die 1 sigma:		
Avg:	1.27	nm
RMS:	1.29	nm
Ellipticity Avg:	1.04	
FOV:	800	nm

C70P140 (BCH\*)



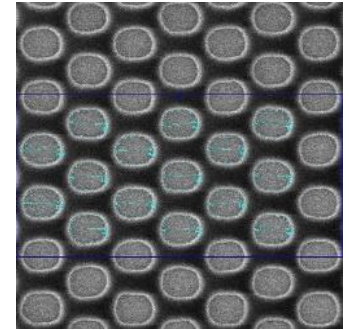
Full Wafer Avg CD:	86.3	nm
Full wafer 1sigma CD:	2.03	nm
Die-to-Die 1 sigma:		
Avg:	1.31	nm
RMS:	1.32	nm
Ellipticity Avg:	1.04	
FOV:	800	nm

C70P140HEX (NCH\*)



Full Wafer Avg CD:	67.38	nm
Full wafer 1sigma CD:	2.63	nm
Die-to-Die 1 sigma		
Avg:	1.78	nm
RMS:	1.79	nm
Ellipticity Avg:	1.21	
FOV:	800	nm

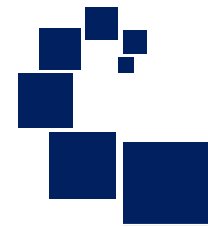
C80P165MEM (ECH2\*)



Full Wafer Avg CD:	94.6	nm
Full wafer 1sigma CD:	1.41	nm
Die-to-Die 1 sigma		
Avg:	1.41	nm
RMS:	1.44	nm
Ellipticity Avg:	1.22	
FOV:	1000	nm

\* Coding labels for CD data results files





# 46IZS107SJG5(2240EMEM002 slot 4) Reference Data

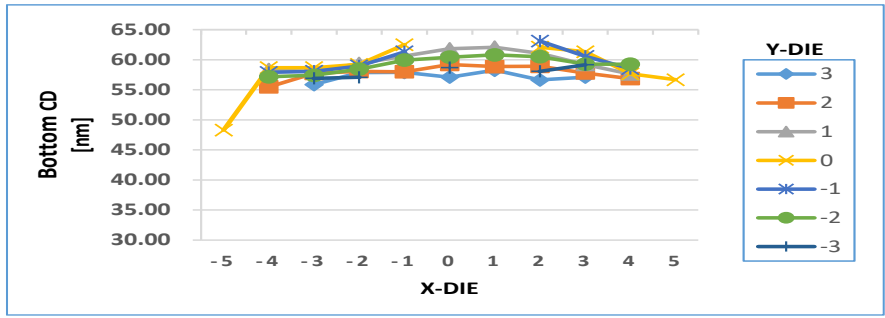
## C60P121 Anchor Target Oct 2022

- All measurements in nm.
- Avg CD and 1sigma line-to-line variation for C60P120 anchor target for each die, reported for each die in wafer map format, and plotted to right.
- Average and 1sigma values are of 8 lines sampled at each site, from images on next page.
- CD values convey top CD of the holes.

Full Wafer Avg CD:	58.66	nm	Average of all individual die CD averages (25 targets/die).
Full wafer 1sigma CD:	2.23	nm	Stdev of all die CD average of (25 targets/die), represents across wafer variation.
Die-to-Die 1sigma			Feature-to-feature variation within grating.
Avg:	1.72	nm	Arithmetic average value of feature-to-feature variation.
RMS:	1.77	nm	RMS average value of feature-to-feature variation.
Ellipticity Avg:	1.05		Average of ratio of major axis to minor axis.
FOV:	800	nm	Size of image (field-of-view).

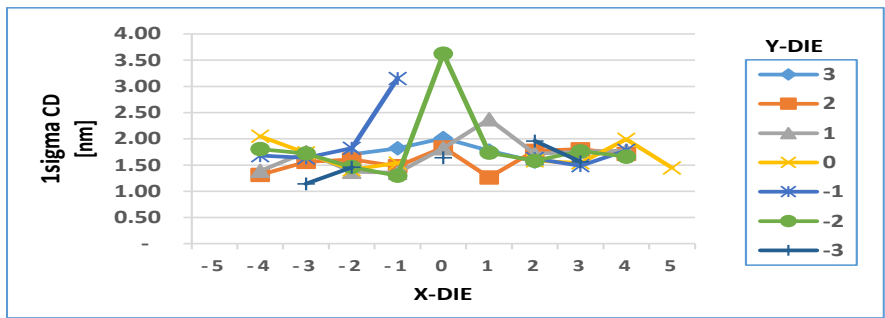
### C60P120 Anchor Target Avg CD (line)

	-5	-4	-3	-2	-1	0	1	2	3	4	5
3			55.86	57.84	57.88	57.09	58.25	56.63	57.09		
2		55.47	57.73	58.05	57.98	59.21	58.85	58.90	57.78	56.85	
1		58.36	58.00	59.37	60.62	61.81	62.08	61.07	59.21	57.63	
0	48.30	58.68	58.68	59.23	62.51			62.08	61.32	57.64	56.67
-1		57.89	58.07	58.96	61.31			63.11	60.56	58.52	
-2		57.17	57.41	58.44	59.94	60.42	60.80	60.50	59.26	59.24	
-3			56.89	57.07		58.68		58.07	59.16		



### C60P120 Anchor Target 1sigma CD

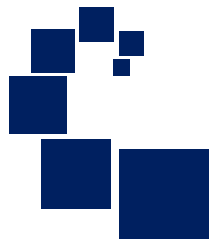
	-5	-4	-3	-2	-1	0	1	2	3	4	5
3				1.71	1.82	2.02	1.77	1.57			
2		1.31	1.56	1.61	1.48	1.84	1.26	1.77	1.80	1.71	
1		1.39	1.75	1.37	1.35	1.82	2.37	1.72	1.76	1.78	
0		2.05	1.73	1.41	1.54			1.58	1.54	1.99	1.45
-1		1.68	1.64	1.82	3.15			1.62	1.49	1.78	
-2		1.80	1.72	1.46	1.30	3.62	1.74	1.58	1.76	1.66	
-3			1.14	1.46		1.64		1.96	1.56		



# 46IZS107SJG5(2240EMEM002 slot 4) Reference Data

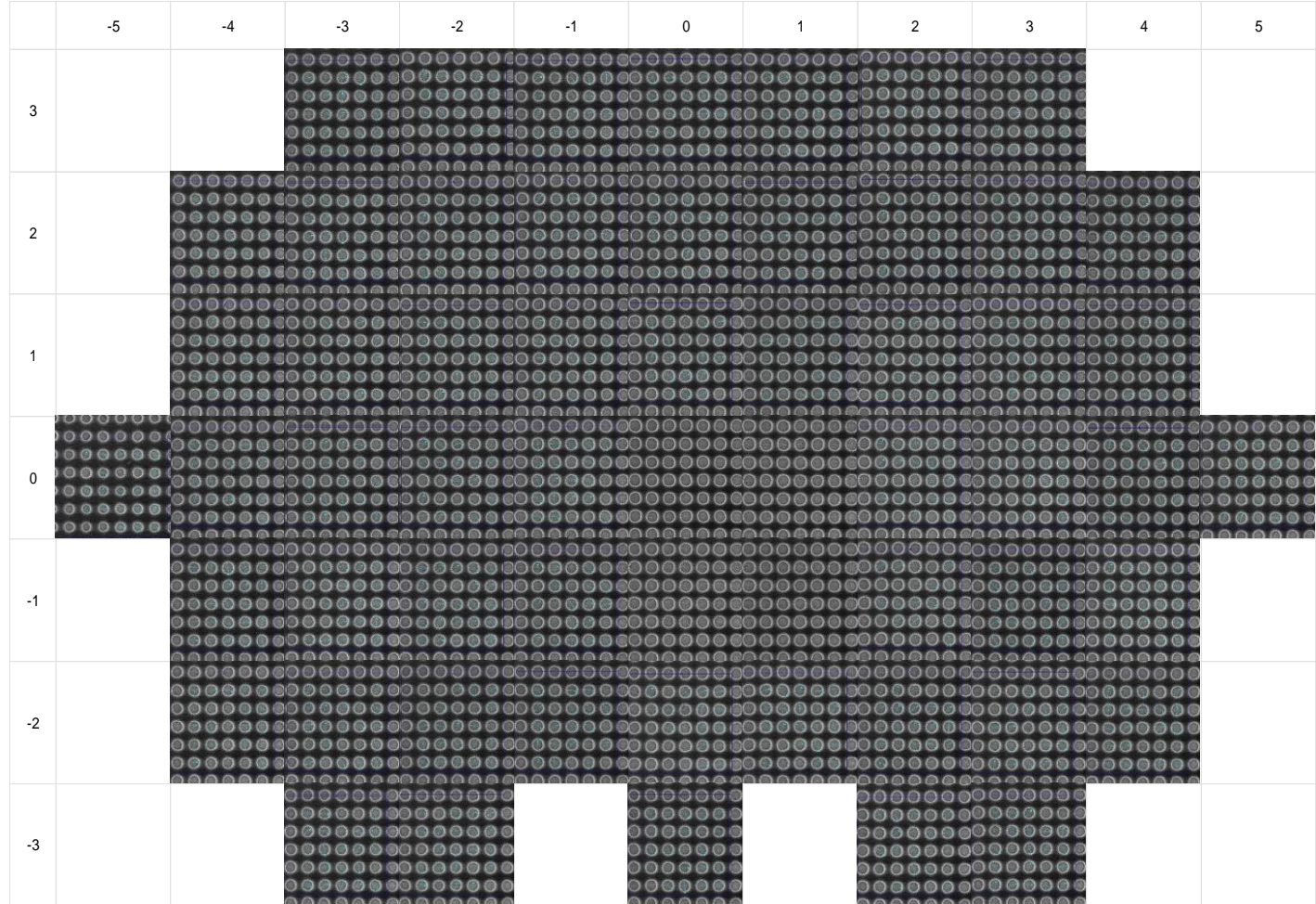
C60P120 Anchor Target

Oct 2022



## C60P120 Anchor Target CD-SEM image wafer map

Full Wafer Avg CD:	58.66	nm
Full wafer 1sigma CD:	2.23	nm
Die-to-Die 1sigma		
Avg:	1.72	nm
RMS:	1.77	nm
Ellipticity Avg:	1.05	
FOV:	800	nm

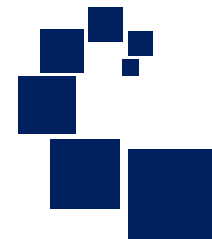




# 46IZS107SJG5(2233EMEM002 slot 4) Reference Data

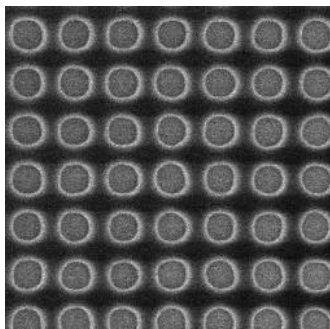
C60P120 Anchor Target

Oct 2022



## Anchor Target

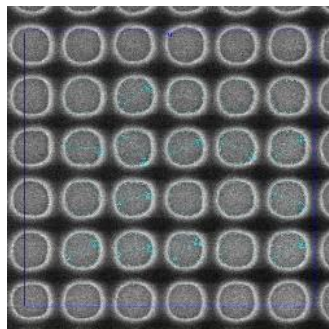
C60P120 (XCH\*)



Full Wafer Avg CD:	58.66	nm
Full wafer 1sigma CD:	2.23	nm
Die-to-Die 1sigma		
Avg:	1.72	nm
RMS:	1.77	nm
Ellipticity Avg:	1.05	
FOV:	800	nm

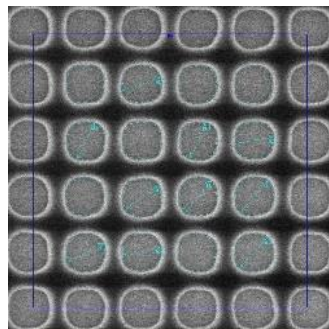
## Secondary Targets

C64P128 (ACH\*)



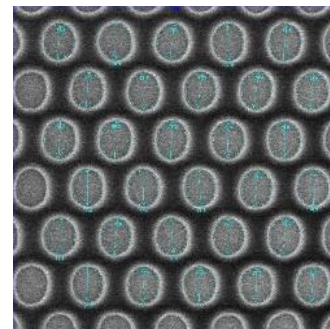
Full Wafer Avg CD:	76.6	nm
Full wafer 1sigma CD:	2.00	nm
Die-to-Die 1 sigma:		
Avg:	1.29	nm
RMS:	1.30	nm
Ellipticity Avg:	1.04	
FOV:	800	nm

C70P140 (BCH\*)



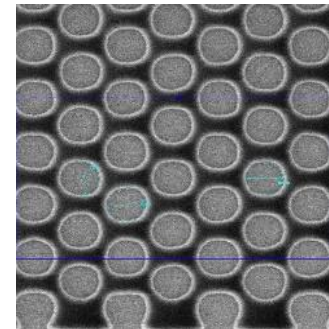
Full Wafer Avg CD:	89.5	nm
Full wafer 1sigma CD:	1.66	nm
Die-to-Die 1 sigma:		
Avg:	1.08	nm
RMS:	1.11	nm
Ellipticity Avg:	1.04	
FOV:	800	nm

C70P140HEX (NCH\*)



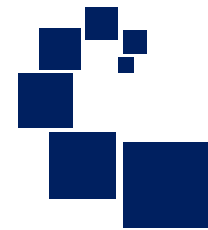
Full Wafer Avg CD:	73.34	nm
Full wafer 1sigma CD:	2.07	nm
Die-to-Die 1 sigma:		
Avg:	1.51	nm
RMS:	1.54	nm
Ellipticity Avg:	1.24	
FOV:	800	nm

C80P165MEM (ECH2\*)



Full Wafer Avg CD:	97.3	nm
Full wafer 1sigma CD:	1.95	nm
Die-to-Die 1 sigma:		
Avg:	2.98	nm
RMS:	5.44	nm
Ellipticity Avg:	1.19	
FOV:	1000	nm

\* Coding labels for CD data results files



# 46IZS106SJC3(2233EMEM002 slot 5) Reference Data

## C60P120 Anchor Target

Oct 2022

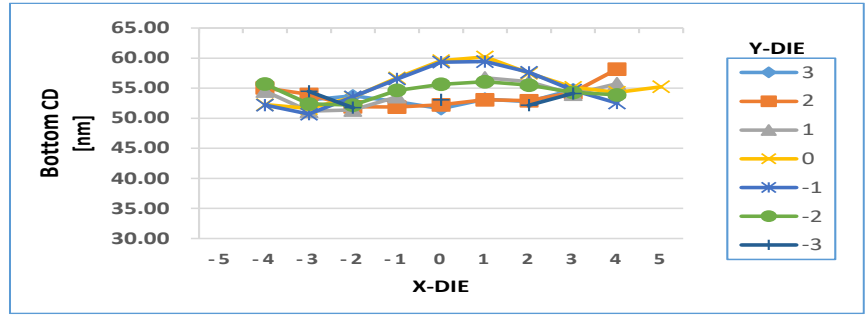
- All measurements in nm.
- Avg CD and 1sigma line-to-line variation for C60P120 anchor target for each die, reported for each die in wafer map format, and plotted to right.
- Average and 1sigma values are of 8 lines sampled at each site, from images on next page.
- CD values convey top CD of the holes.

Full Wafer Avg CD:	54.33	nm
Full wafer 1sigma CD:	2.28	nm
Die-to-Die 1sigma		
Avg:	1.73	nm
RMS:	1.74	nm
Ellipticity Avg:	1.05	
FOV:	800	nm

Average of all individual die CD averages (25 targets/die).  
 Stdev of all die CD average of (25 targets/die), represents across wafer variation.  
 Feature-to-feature variation within grating.  
 Arithmetic average value of feature-to-feature variation.  
 RMS average value of feature-to-feature variation.  
 Average of ratio of major axis to minor axis.  
 Size of image (field-of-view).

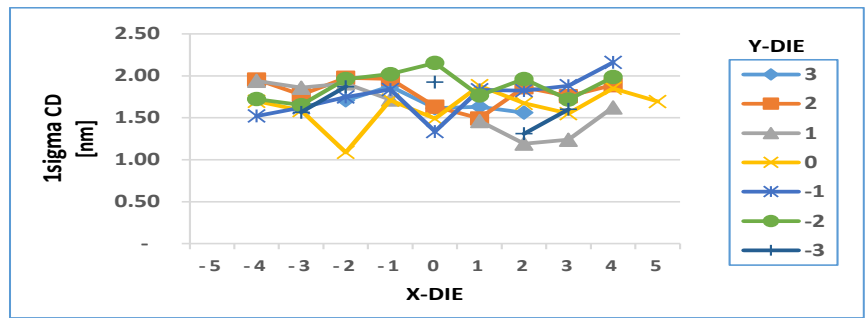
### C60P120 Anchor Target Avg CD (line)

	-5	-4	-3	-2	-1	0	1	2	3	4	5
3			53.03	53.72	52.75	51.58	53.16	52.74	54.73		
2		55.04	53.96	51.90	51.85	52.22	53.07	52.91	54.29	58.17	
1		54.51	51.18	51.38	53.57		56.72	56.07	53.97	55.75	
0		52.26	51.61	53.47	56.71	59.57	60.20	57.49	55.13	54.30	55.23
-1		52.17	50.67	53.55	56.52	59.32	59.43	57.65	54.66	52.53	
-2		55.68	52.38	52.17	54.62	55.63	56.07	55.50	54.28	53.88	
-3			54.46	51.76		53.07		52.15	54.13		



### C60P120 Anchor Target 1sigma CD

	-5	-4	-3	-2	-1	0	1	2	3	4	5
3				1.71	1.88	1.62	1.63	1.56			
2		1.96	1.77	1.98	1.96	1.63	1.49	1.86	1.76	1.89	
1		1.94	1.86	1.91	1.72		1.46	1.19	1.24	1.63	
0		1.70	1.59	1.09	1.71	1.49	1.88	1.67	1.55	1.85	1.69
-1		1.52	1.62	1.75	1.84	1.34	1.83	1.82	1.88	2.16	
-2		1.72	1.65	1.96	2.02	2.15	1.77	1.96	1.72	1.99	
-3			1.57	1.87		1.93		1.31	1.60		

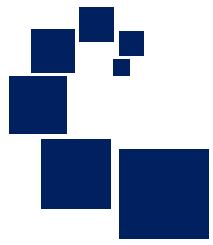




# 46IZS106SJC3(2233EMEM002 slot 5) Reference Data

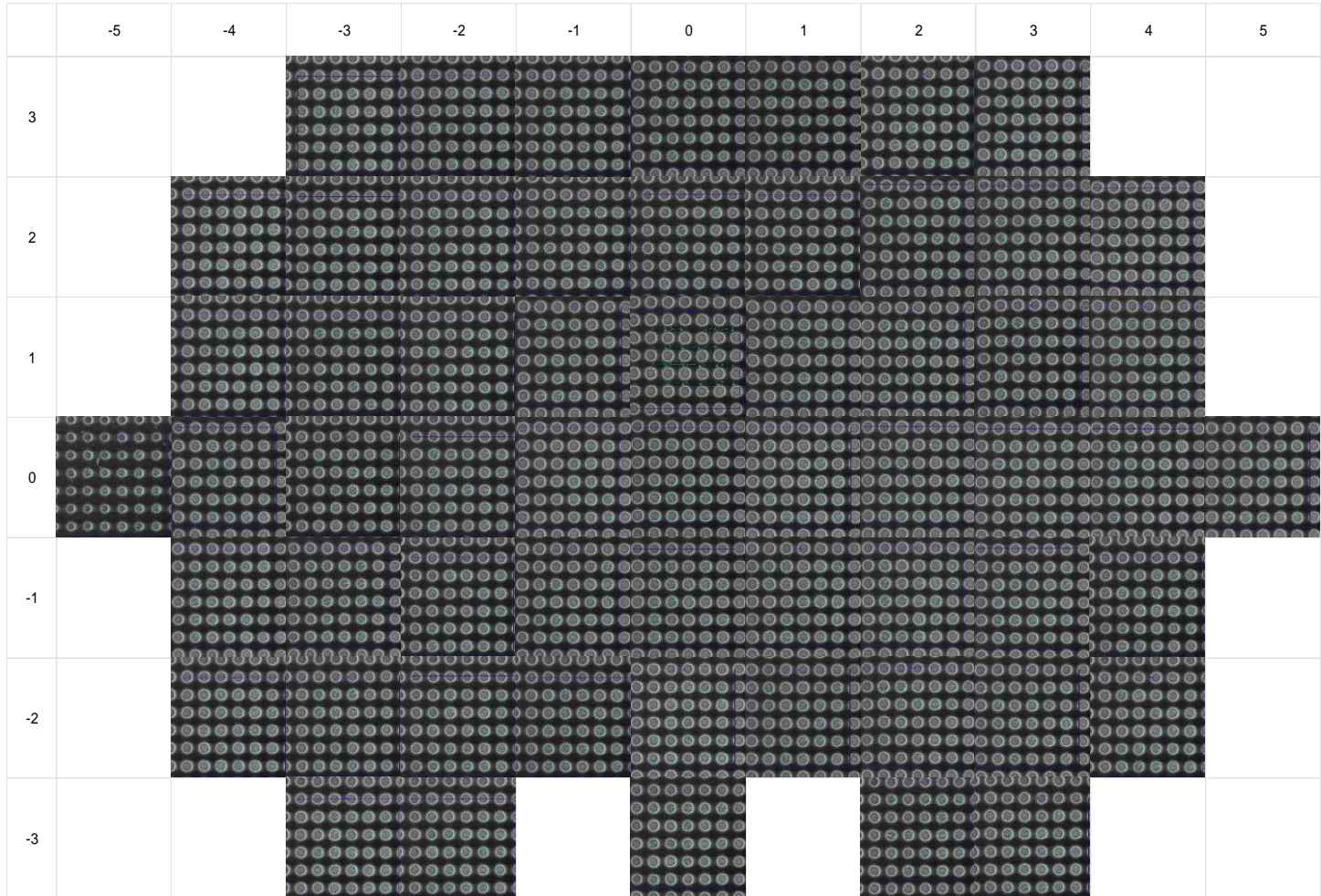
C60P120 Anchor Target

Oct 2022



## C60P120 Anchor Target CD-SEM image wafer map

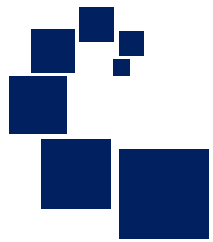
Full Wafer Avg CD:	54.33	nm
Full wafer 1sigma CD:	2.28	nm
Die-to-Die 1sigma		
Avg:	1.73	nm
RMS:	1.74	nm
Ellipticity Avg:	1.05	
FOV:	800	nm



# 46IZS106SJC3(2233EMEM002 slot 5) Reference Data

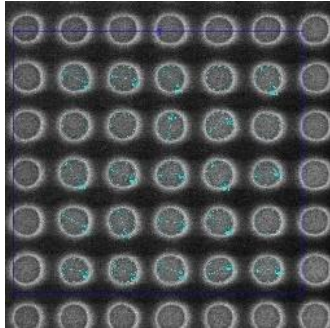
C60P120 Anchor Target

Oct 2022



## Anchor Target

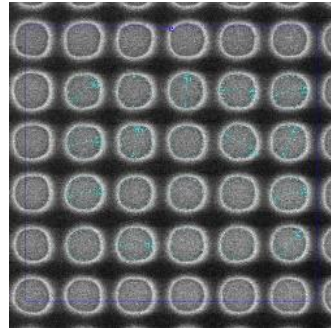
C60P120 (XCH\*)



Full Wafer Avg CD:	54.33	nm
Full wafer 1sigma CD:	2.28	nm
Die-to-Die 1sigma		
Avg:	1.73	nm
RMS:	1.74	nm
Ellipticity Avg:	1.05	
FOV:	800	nm

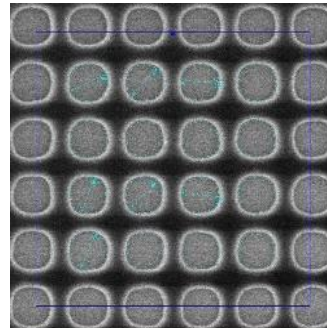
## Secondary Targets

C64P128 (ACH\*)



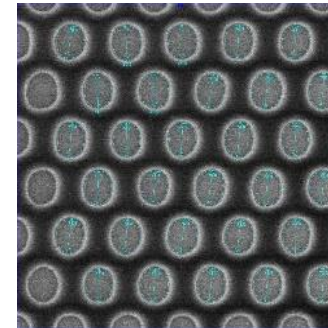
Full Wafer Avg CD:	72.7	nm
Full wafer 1sigma CD:	1.92	nm
Die-to-Die 1 sigma:		
Avg:	1.34	nm
RMS:	1.35	nm
Ellipticity Avg:	1.04	
FOV:	800	nm

C70P140 (BCH\*)



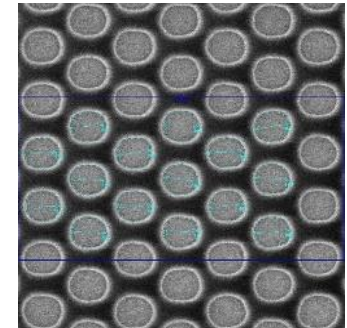
Full Wafer Avg CD:	85.7	nm
Full wafer 1sigma CD:	1.77	nm
Die-to-Die 1 sigma:		
Avg:	1.24	nm
RMS:	1.27	nm
Ellipticity Avg:	1.03	
FOV:	800	nm

C70P140HEX (NCH\*)



Full Wafer Avg CD:	92.8	nm
Full wafer 1sigma CD:	5.88	nm
Die-to-Die 1 sigma		
Avg:	3.93	nm
RMS:	8.77	nm
Ellipticity Avg:	1.24	
FOV:	1000	nm

C80P165MEM (ECH2\*)



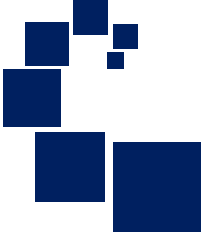
Full Wafer Avg CD:	68.61	nm
Full wafer 1sigma CD:	2.32	nm
Die-to-Die 1 sigma		
Avg:	1.48	nm
RMS:	1.49	nm
Ellipticity Avg:	1.28	
FOV:	800	nm

\* Coding labels for CD data results files

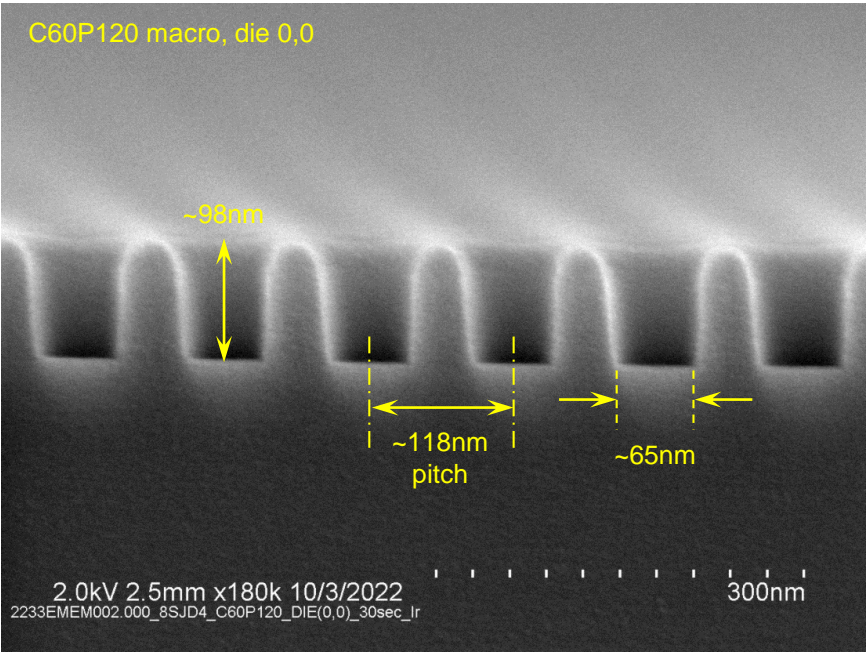


# C60P120 Target XSEM Reference Data

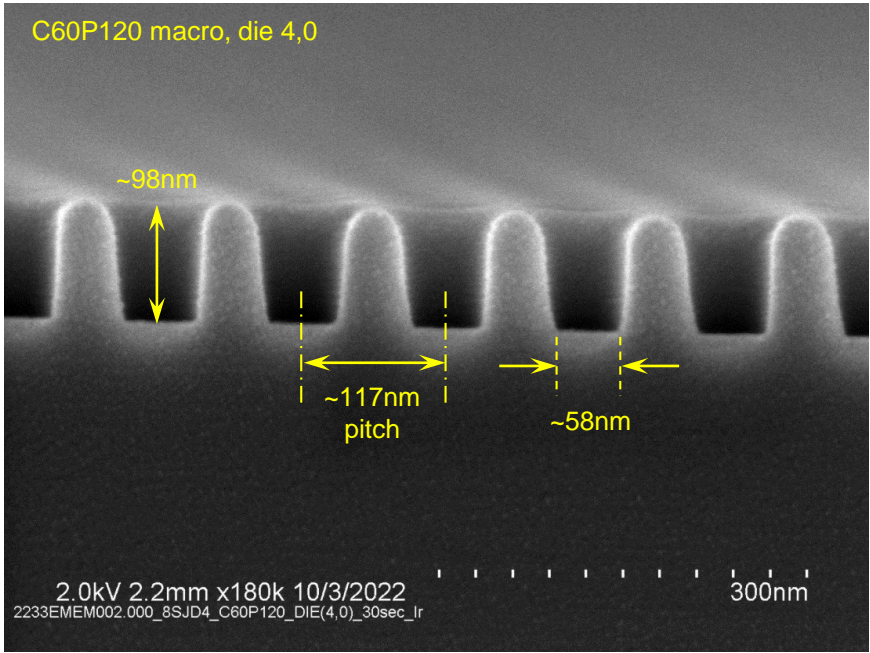
Oct 2022



## Target XSEM images

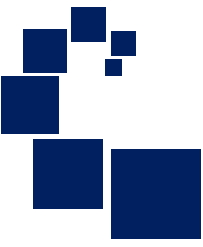


Center



Edge

# Conclusions

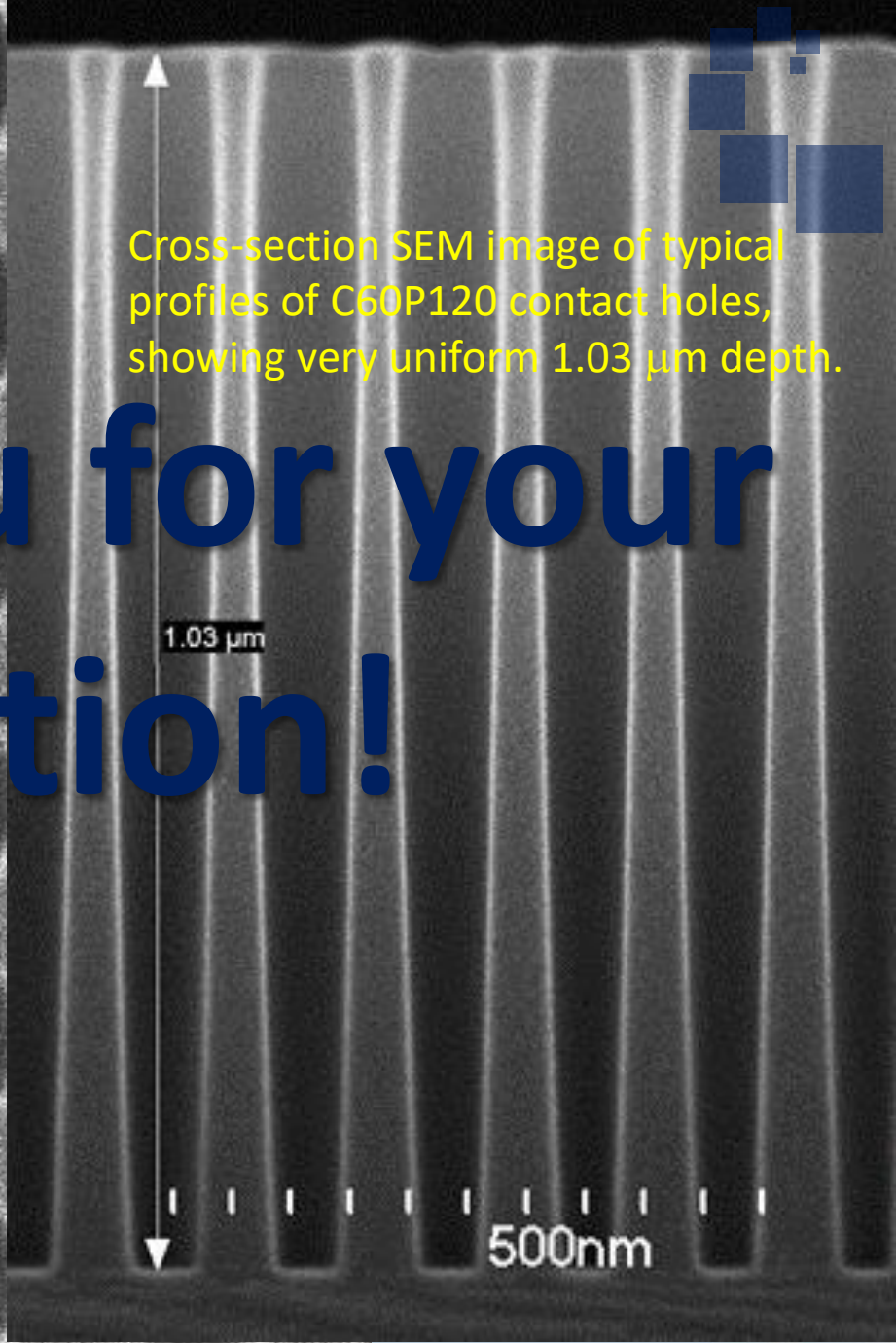


- Thank you for your purchase of AMAG wafers!
- We hope this guide of reference CD-SEM metrology adds significant value to the use of these wafers.
- This report represents the standard metrology AMAG nanometro provides for such wafers, and future lots and wafer types will have similar companion data sets.





Top down CD-SEM image of typical C60P120 grating. FOV = 660 nm.  
Note image cropped on right.



Cross-section SEM image of typical profiles of C60P120 contact holes, showing very uniform 1.03 μm depth.

# Thank you for your Attention!